

Isc N-Channel MOSFET Transistor

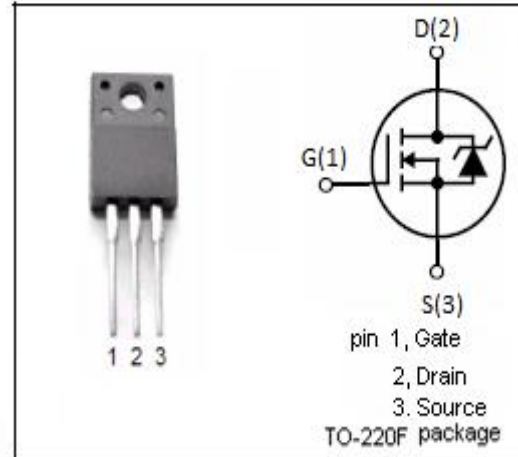
IPA80R1K4CE

• FEATURES

- With TO-220F package
- Low input capacitance and gate charge
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

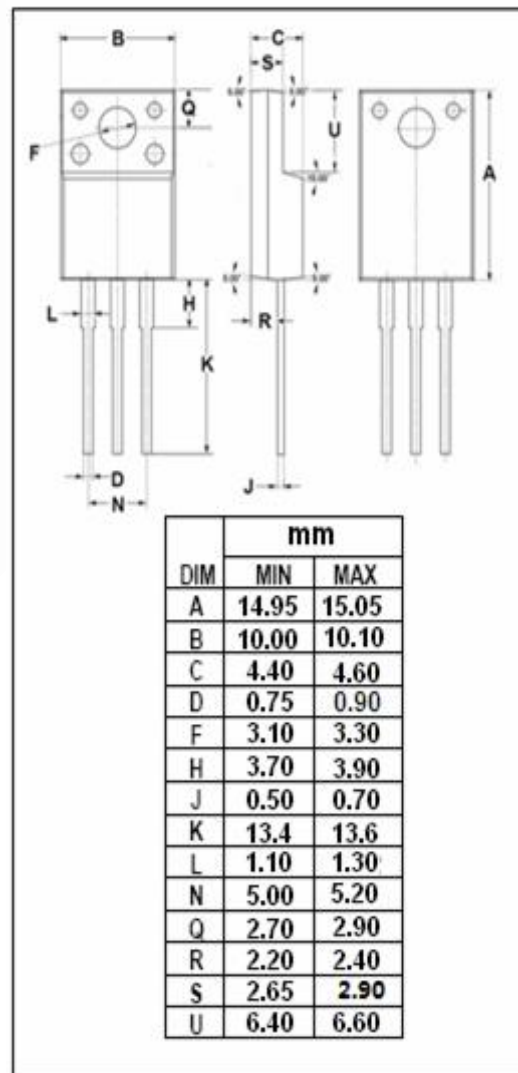
• APPLICATIONS

- Switching applications



• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	800	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous @T _c =25°C (V _{GS} at 10V) T _c =100°C	3.9 2.3	A
I _{DM}	Drain Current-Single Pulsed	12	A
P _D	Total Dissipation @T _c =25°C	38	W
T _j	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	4.0	°C/W
Rth(ch-a)	Channel-to-ambient thermal resistance	80	°C/W

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	800			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.24mA	2.1		3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =2.3A		1220	1400	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 800V; V _{GS} = 0V; T _J =25°C V _{DS} = 800V; V _{GS} = 0V; T _J =150°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =3.9A, V _{GS} = 0V		1.0		V